TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74HCT646AP

Octal Bus Transceiver/Register (3-state)

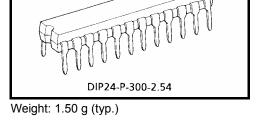
The TC74HCT646A is high speed CMOS OCTAL BUS TRANSCEIVER/REGISTERs fabricated with silicon gate C<sup>2</sup>MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Its inputs are compatible with TTL, NMOS, and CMOS output voltage levels.

This device is bus transceiver with 3-state outputs, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the internal registers.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.



#### Features (Note 1)(Note 2)

- High speed:  $f_{max} = 60 \text{ MHz}$  (typ.) at  $V_{CC} = 5 \text{ V}$
- Low power dissipation:  $I_{CC} = 4 \mu A \pmod{at Ta} = 25 \circ C$
- Compatible with TTL output: VIH = 2.0 V (min)
- $V_{IL} = 0.8 V (max)$
- Output drive capability: 15 LSTTL loads
- Symmetrical output impedance: |IOH| = IOL = 6 mA (min)
- Balanced propagation delays:  $t_{pLH} \simeq t_{pHL}$
- Pin and function compatible with 74LS646

Note 1: Do not apply a signal to any bus terminal when it is in the output mode. Damage may result.

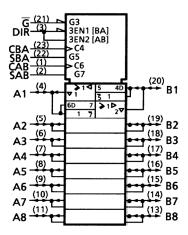
Note 2: All floating (high impedance) bus terminals must have their input levels fixed by means of pull up or pull down resistors.

#### **Pin Assignment**

	1 H		v
CAB	1 🖸	✓ □ 24	$V_{cc}$
SAB	2	23	CBA
DIR	3 🗖	22	SBA
A1	4 🗹	23 22 21	G
A2	5 🗖	<b>1</b> 20	B1
A3	6 <b>C</b> 7 <b>C</b>	<b>1</b> 19	B2
A4	7 🗖	18	B3
A5	8 0	<b>þ</b> 17	B4
A6	9 🛛	20 19 18 17 16 15 14 13	B5
A7	10 🔲	15	B6
A8	11 <b>[</b>	14	B7
GND	12 <b>[</b>	13	B8
	(700		
	(IOP	VIEW)	



#### **IEC Logic Symbol**



#### **Truth Table**

G	DIR	CAB	CBA	SAB	SBA	А	В	Function
	X	X (Note)	X (Note)	х	х	Inputs Z	Inputs Z	The output functions of A and B busses are disabled.
Н	Х			х	x	х	х	Both A and B busses are used as inputs to the internal flip-flops. Data on the bus will be stored on the rising edge of the clock.
		х	х			Inputs	Outputs	
		^ (Note)	^ (Note)	L	х	L	L	The data on the A bus are displayed on the B bus.
		(Note)	(14018)			Н	Н	
			х		×	L	L	The data on the A bus are displayed on the B bus,
L	L H	+	(Note)	L	Х	Н	Н	and are stored into the A storage flip-flops on the rising edge of CAB.
		X (Note)	Х	н	x	х	Qn	The data in the A storage flip-flops are displayed
			(Note)	п	^			on the B bus.
		<u> </u>	х	н	x	L	L	The data on the A bus are stored into the A storage flip-flops on the rising edge of CAB, and
			(Note)	п	^	Н	Н	the stored data propagate directly onto the B bus.
		х	v			Outputs	Inputs	
		X X (Note) (Note)	х	L	L	L	The data on the B bus are displayed on the A bus.	
		(NOLE)	(NOLE)			Н	н	
		х		х	L	L	L	The data on the B bus are displayed on the A bus, and are stored into the B storage flip-flops on the
L	L	L (Note)		~	L	Н	Н	rising edge of CBA.
		х	х	х	н	Qn	х	The data in the B storage flip-flops are displayed
		(Note)	(Note)	^	11		^	on the A bus.
		х	_	х	н	L	L	The data on the B bus are stored into the B storage flip-flops on the rising edge of CBA, and
		(Note)		^	П	Н	Н	the stored data propagate directly onto the A bus.

#### X: Don't care

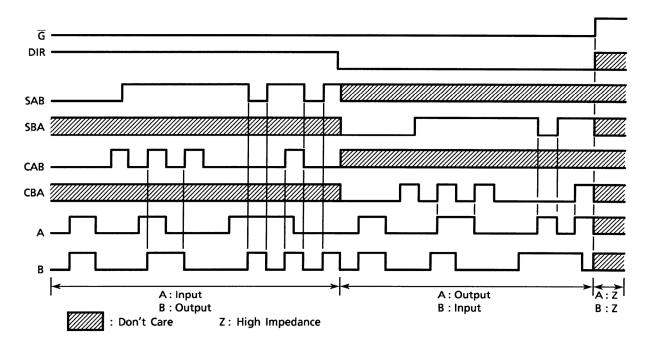
Qn: The data stored into the internal flip-flops by most recent low to high transition of the clock inputs.

Z: High impedance

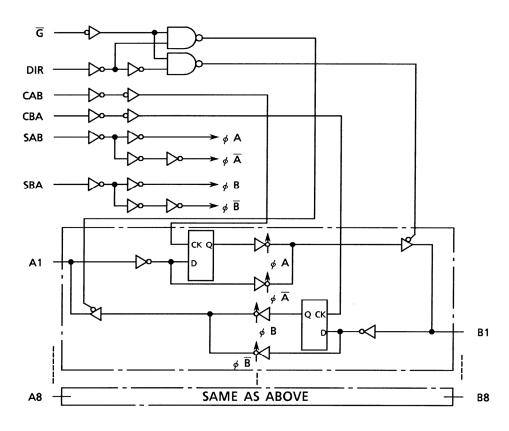
Note: The clock are not internally gated with either  $\overline{G}$  or DIR. Therefore, data on the A and/or B busses may be clocked into the storage flip-flops at any time.

## **TOSHIBA**

#### **Timing Chart**



#### System Diagram



#### Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	mbol Rating	
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~V <sub>CC</sub> + 0.5	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	I <sub>IK</sub>	±20	mA
Output diode current	IOK	±20	mA
DC output current	IOUT	±35	mA
DC V <sub>CC</sub> /ground current	ICC	±75	mA
Power dissipation	PD	500 (DIP) (Note 2)	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C should be applied up to 300 mW.

Characteristics	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	4.5~5.5	V
Input voltage	V <sub>IN</sub>	0~V <sub>CC</sub>	V
Output voltage	V <sub>OUT</sub>	0~V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	t <sub>r</sub> , t <sub>f</sub>	0~500	ns

#### **Operating Ranges (Note)**

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

#### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics	Symbol	Test Condition		-	Ta = 25°C			Ta = -40~85°C		
Characteristics	Symbol		V <sub>CC</sub>		Min	Тур.	Max	Min	Max	Unit
High-level input voltage	V <sub>IH</sub>	—		4.5~5.5	2.0	_	_	2.0	_	V
Low-level input voltage	V <sub>IL</sub>	—		4.5~5.5	_	_	0.8		0.8	V
High-level output	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -20 \ \mu A$	4.5	4.4	4.5		4.4	_	V
voltage	VOH		$I_{OH} = -6 \text{ mA}$	4.5	4.18	4.31		4.13		v
Low-level output	V <sub>OL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 20 \ \mu A$	4.5		0.0	0.1		0.1	V
voltage			$I_{OL} = 6 \text{ mA}$	4.5		0.17	0.26	_	0.33	v
3-state output off state current	I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or } GND$		5.5		—	±0.5		±5.0	μΑ
Input leakage current	IIN	$V_{IN} = V_{CC}$ or GND		5.5			±0.1		±1.0	μA
Quiescent supply current	Icc	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5		_	4.0		40.0	μA
	$I_C$ Per input: $V_{IN} = 0.5 V$ of Other input: $V_{CC}$ or GN			5.5	_	_	2.0		2.9	mA

#### Timing Requirements (input: $t_r = t_f = 6 \text{ ns}$ )

Characteristics	Symbol	Test Condition	Test Condition			Ta = _40 ~85°C	Unit	
			V <sub>CC</sub> (V)	Тур.	Limit	Limit		
Minimum pulse width	t <sub>W (L)</sub>		4.5	_	15	19	20	
(CK)	t <sub>W (H)</sub>	_	5.5	—	14	17	ns	
Minimum set-up time	ts		4.5	_	10	13	ns	
Minimum set-up time			5.5	—	9	12		
Minimum hold time	+.		4.5	_	5	5	ns	
	t <sub>h</sub>	_	5.5	—	5	5	115	
Clock fraguenou	f		4.5	_	31	25	MHz	
Clock frequency	I	_	5.5	—	37	30	IVIHZ	

#### AC Characteristics (input: $t_r = t_f = 6 \text{ ns}$ )

Characteristics	Symbol	Test Condition			-	Га = 25°С	)	Ta = -4	0~85°C	Unit
Characteristics	Symbol		CL (pF)	$V_{CC}(V)$	Min	Тур.	Max	Min	Max	Unit
Output transition time	t <sub>TLH</sub>		50	4.5	—	7	12	_	15	ns
	t <sub>THL</sub>		50	5.5		6	11	—	14	
<b>D</b>			50	4.5	_	20	30	—	38	ns
Propagation delay time	t <sub>pLH</sub>		00	5.5		17	27	—	34	
(BUS-bus)	t <sub>pHL</sub>		150	4.5	_	25	38	—	48	110
			100	5.5	_	22	34	_	43	
Dreperation dalay			50	4.5		29	44	—	55	
Propagation delay time	t <sub>pLH</sub>			5.5	_	26	40	_	50	ns
(CAB, CBA-bus)	t <sub>pHL</sub>		150	4.5		34	52	—	65	
			100	5.5	_	31	47	—	59	
Decementing delays			50	4.5		24	34	—	43	
Propagation delay time	t <sub>pLH</sub>			5.5	_	21	31	_	39	ns
(SAB, SBA-bus)	t <sub>pHL</sub>		150	4.5	_	— 29	42	—	53	
			100	5.5	_	26	38	—	46	
		R <sub>L</sub> = 1 kΩ	50	4.5	_	26	38	—	48	
Output enable time	t <sub>pZL</sub>		00	5.5	_	23	34	—	43	ns
(DIR, G-bus)	t <sub>pZH</sub>		150	4.5	_	31	46	—	58	115
			100	5.5		28	41	—	52	
Output disable time	t <sub>pLZ</sub>	$R_L = 1 k\Omega$	50	4.5	_	26	35	—	44	ns
(DIR, G -bus)	t <sub>pHZ</sub>	112 - 1 132	50	5.5		23	32	—	40	113
Maximum clock	f <sub>max</sub>		50	4.5	31	55	—	25		MHz
frequency	imax		50	5.5	37	61	_	30	_	
Input capacitance	C <sub>IN</sub>	DIR, $\overline{G}$ , SAB, SBA, CAB, CBA				5	10	—	10	pF
Output capacitance	C <sub>I/O</sub>	An, Bn				13	—	_		pF
Power dissipation capacitance	C <sub>PD</sub> (Note)	_	_			40	_	_	_	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

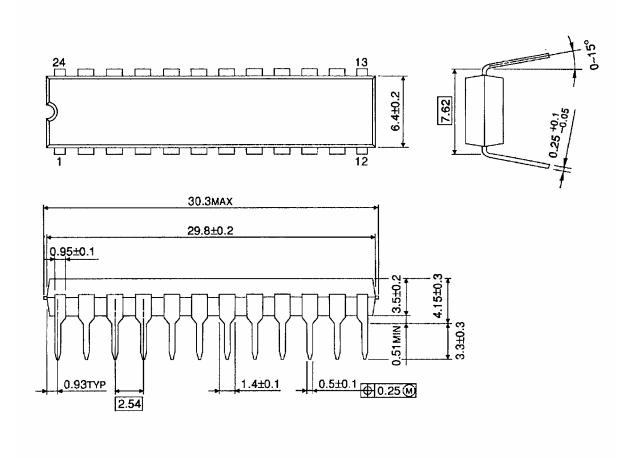
 $I_{CC}$  (opr) =  $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$  (per bit)

## TOSHIBA

### Package Dimensions

DIP24-P-300-2.54

Unit : mm



Weight: 1.50 g (typ.)

#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN GENERAL

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.).These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patents or other rights of TOSHIBA or the third parties.
- Please contact your sales representative for product-by-product details in this document regarding RoHS compatibility. Please use these products in this document in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses occurring as a result of noncompliance with applicable laws and regulations.